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Abstract

The data included in this article provides additional supplementary information on our recent publication describing "Inducing tunable switching behavior in a single memristor" [1]. Analyses of micro/nano-structural and compositional changes induced in a resistive oxide memory during resistive switching are carried out. Chromium doped strontium titanate based resistance change memories are fabricated in a capacitor-like metal-insulator-metal structure and subjected to different biasing conditions to set memory states. Transmission electron microscope based cross-sectional analyses of the memory devices in different memory states are collected and presented.

Specifications Table

Subject area	*Electrical Engineering, Material Science*
More specific subject area	*Resistive oxide memories, Interface engineering*
Type of data	*Image (Transmission electron microscopy, electron energy loss spectroscopy, energy-dispersive X-ray spectroscopy)*
How data was acquired	*Cross-sectional lamellae are prepared by focused ion beam (FIB) cuts by*

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